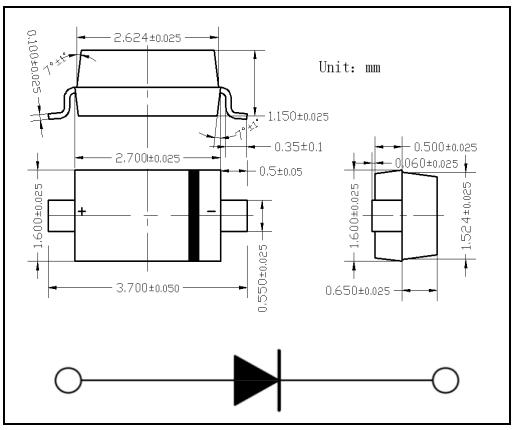
SOD-123 Plastic-Encapsulate Diodes

BAV20W

Switching Diode



Features

- Low Reverse Current
- Surface Mount Package Ideally Suited for Automatic Insertion
- Fast Switching Speed
- For General Purpose Switching Applications

Marking: T2

Maximum Ratings (T_a=25°C unless otherwise noted)

Symbol	Parameter	Value	Unit
V_{RM}	Non-Repetitive Peak Reverse Voltage	200	V
V_{RRM}	Peak Repetitive Peak Reverse Voltage	150	V
V_{RWM}	Working peak reverse voltage		V
$V_{R(RMS)}$	RMS reverse voltage	106	V
I_O	Average Rectified Output Current	200	mA
I_{FSM}	Non-Repetitive Peak Forward Surge Current @ t=8.3ms	2.0	A
P_D	Power Dissipation	500	mW
$R_{\theta JA}$	Thermal Resistance from Junction to Ambient	250	°C/W
T_j	Junction Temperature	150	°C
T_{stg}	Storage Temperature	-55~+150	°C

Electrical Characteristics (T_a=25°C unless otherwise specified)

Symbol	Parameter	Test Conditions	Min	Typ	Max	Unit
$V_{(BR)}$	Reverse breakdown voltage	I_R = 100μA	200			V
I_R	Reverse current	V_R = 150V			0.1	μA
V_F	Forward voltage	I_F = 100mA			1	V
		I_F = 200mA			1.25	V
C_{tot}	Total capacitance	V_R = 0V,f = 1MHz			5	pF
t_{rr}	Reverse recovery time	I_F = I_R = 30mA, I_{rr} = 0.1*I_R , R_L=100Ω			50	ns

Typical Characteristics